DATA SHEET



PNP SILICON TRANSISTOR **2SA1626**

DESCRIPTION The 2SA1626 is designed for general purpose amplifier and high

speed switching applications.

FEATURES

- High Voltage.
- High Speed Switching.
- Low Collector Saturation Voltage.

ABSOLUTE MAXIMUM RATINGS

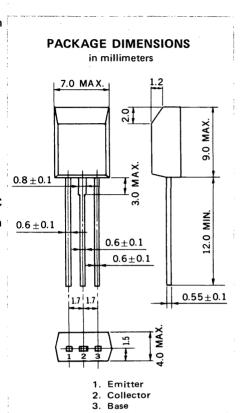
Maximum Temperatures

Total Power Dissipation 1.0

Maximum Voltages and Currents ($T_0 = 25^{\circ}C$)

	vortages and carrents (1a 25 c)		
V_{CBO}	Collector to Base Voltage400	V	
V_{CEO}	Collector to Emitter Voltage400	V	
V_{EBO}	Emitter to Base Voltage -7.0	V	
I _C	Collector Current (DC)2.0	Α	
Ic	Collector Current (pulse)*4.0	Α	

^{*} PW \leq 10 ms, Duty Cycle \leq 50 %



ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
hFE1**	DC Current Gain	40	60	120	-	$V_{CE} = -5.0 \text{ V, I}_{C} = -0.1 \text{ A}$
hFE2**	DC Current Gain	6	22		-	$V_{CE} = -5.0 \text{ V}, I_{C} = -1.0 \text{ A}$
fŢ	Gain Bandwidth Product	10	40		MHz	$V_{CE} = -10 \text{ V, I}_{E} = 0.1 \text{ A}$
C _{ob}	Output Capacitance	4	30	40	pF	$V_{CB} = -10 \text{ V}, I_{E} = 0, f = 1.0 \text{ MHz}$
ICBO	Collector Cutoff Current			-10	μΑ	$V_{CB} = -400 \text{ V}, I_{E} = 0$
IEBO	Emitter Cutoff Current			-10	μΑ	$V_{EB} = -5.0 \text{ V}, I_{C} = 0$
VCE(sat)**	Collector Saturation Voltage		-0.25	-0.5	V	$I_C = -0.5 \text{ A}, I_B = -0.1 \text{ A}$
V _{BE(sat)} **	Base Saturation Voltage		-0.85	-1.2	V	$I_C = -0.5 \text{ A}, I_B = -0.1 \text{ A}$
ton	Turn On Time		0.03	0.5	μs	$I_{C} = -1.0 \text{ A, R}_{L} = 150 \Omega$
t _{stg}	Storage Time		1.4	2.0	μs	$I_{B1} = -I_{B2} = -0.2 \text{ A}$
tf	Fall Time		0.1	0.7	μs	V _{CC} = -150 V

^{**} Pulsed PW \leq 350 μ s, Duty Cycle \leq 2 %

Classification of h_{FE1}

Rank	L	К		
Range	40 to 80	60 to 120		

Test Conditions: $V_{CE} = -5.0 \text{ V}$, $I_{C} = -0.1 \text{ A}$

TYPICAL CHARACTERISTICS ($T_a = 25$ °C)

